

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L12	3	((ozonate or ozonating or ozonation or ozonated) near deionized near water) same (dielectric or insulating or oxide or nitride or sin) same (anneal or annealing or annealed or treat or treating or treated or treatment)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:31
L13	5	((ozonate or ozonating or ozonation or ozonated) near deionized near water) and (dielectric or insulating or oxide or nitride or sin) and (anneal or annealing or annealed)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:32
L14	620	(gate near2 substrate near2 capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:33
L15	2	(gate near2 substrate near2 capacitance) and (oxide near2 nitride near2 gate near2 (insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:34
L16	117	(oxide near2 nitride near2 stack).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:34
L17	16	(method near5 oxide near2 nitride near2 stack).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:35
L18	11	(method near5 oxide near2 nitride near2 stack).clm. and (oxide near2 (film or layer)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:35
L19	11	(method near5 oxide near2 nitride near2 stack).clm. and (nitride near10 (oxide near2 (film or layer))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:36
L20	9	(method near5 oxide near2 nitride near2 stack).clm. and ((nitride near (layer or film)) near10 (oxide near2 (film or layer))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:37

L21	152360	(form or forming or formed or formation) near5 (oxide near (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:38
L22	4183	(form or forming or formed or formation) near5 (oxide near (layer or film)).clm. and (form or forming or formed or formation) near5 (nitride near (layer or film)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:39
L23	2758	(form or forming or formed or formation) near5 (oxide near (layer or film)).clm. same(form or forming or formed or formation) near5 (nitride near (layer or film)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:39
L24	2758	(form or forming or formed or formation) near5 (oxide near (layer or film)).clm. same (form or forming or formed or formation) near5 (nitride near (layer or film)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:39
L25	2758	((form or forming or formed or formation) near5 (oxide near (layer or film))) same ((form or forming or formed or formation) near5 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:40
L26	291	(method or process) near5 (((form or forming or formed or formation) near5 (oxide near (layer or film))) same ((form or forming or formed or formation) near5 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:40
L27	122	(method or process) near5 (((form or forming or formed or formation) near3 (oxide near (layer or film))) same ((form or forming or formed or formation) near3 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:40
L28	105	(method or process) near5 (((form or forming or formed or formation) near3 (oxide near (layer or film))) with ((form or forming or formed or formation) near3 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:41

L29	70	(method or process) near5 (((form or forming or formed or formation) near2 (oxide near (layer or film))) with ((form or forming or formed or formation) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:41
L30	30	(method or process) near5 (((forming or depositing) near2 (oxide near (layer or film))) with (((form or forming or formed or formation) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:41
L31	30	(method or process) near5 (((growing or forming or depositing) near2 (oxide near (layer or film))) with ((form or forming or formed or formation) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:42
L32	7	(method or process) near5 (((growing or forming or depositing) near2 (oxide near (layer or film))) with ((growing or depositing) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:43
L33	132	(((growing or forming or depositing) near2 (oxide near (layer or film))) with ((growing or depositing) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:43
L34	4	(oxide near nitride near stack) and (((growing or forming or depositing) near2 (oxide near (layer or film))) with ((growing or depositing) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:44
L35	12	(oxide near nitride near stack) and (((growing or forming or depositing) near2 (oxide near (layer or film))) same ((growing or depositing) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:44
L36	1	(oxide near nitride near stack). clm. and (((growing or forming or depositing) near2 (oxide near (layer or film))) same ((growing or depositing) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:45

L37	1	(oxide near nitride near stack). clm. and (((growing or forming or depositing) near2 (oxide near (layer or film))) and ((growing or depositing) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:45
L38	294	(((growing or forming or depositing) near2 (oxide near (layer or film))) same ((growing or depositing) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:45
L39	15	(((growing or forming or depositing) near2 (oxide near (layer or film))) same ((growing or depositing) near2 (nitride near (layer or film))))).clm. and chamber.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:47
L40	1	(((growing or forming or depositing) near2 (oxide near (layer or film))) with chamber) same ((growing or depositing) near2 (nitride near (layer or film))))).clm. and chamber.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:47
L41	1	(((growing or forming or depositing) near2 (oxide near (layer or film))) with chamber) same ((growing or depositing) near2 (nitride near (layer or film))))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:48
L42	31	(((growing or forming or depositing) near2 (oxide near (layer or film))) with chamber) and (((growing or depositing) near2 (nitride near (layer or film)))) with chamber)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:50
L43	8	(((growing or forming or depositing) near2 (oxide near (layer or film))) with chamber) and (((growing or depositing) near2 (nitride near (layer or film)))) with chamber).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 20:49